

SUBSTRATE PROPERTY	MGSiC6NNA	MGSiC6NNB	MGSiC6NNC
Grade	A	B	C
Diameter	150.0 mm±0.25 mm		
Surface Orientation	4° toward <11-20> ± 0.5°		
Primary Flat Orientation	<11-20> ± 5.0°		
Secondary Flat Orientation	N/A		
Primary Flat Length	47.5 mm ±1.5 mm		
Secondary Flat Length	None		
Wafer Edge	Chamfer		
Carrier Type	n-type		
Dopant	N-doped		
Micropipe Density	≤1 micropipes/ cm ²	≤5 micropipes/ cm ²	≤30 micropipes/ cm ²
Polytype	4H		
Resistivity	0.015 Ω·cm ~ 0.028 Ω·cm		
Thickness	350.0 μm ± 25.0 μm or 500.0 μm ± 25.0 μm		
TTV	≤10 μm		
Bow (absolute value)	≤40 μm		
Warp	≤65 μm		
Surface Finish	C-face: MP, Si-face:CMP		
Surface Roughness	CMP Si Face Ra≤0.5 nm		N/A
Cracks by high-intensity light	None		
Edge chips/indents by diffuse lighting	None	≤2, the length and width of each < 1 nm	
Total usable area	≥90%	≥80%	N/A

*The other specifications can be customized according to customer's requirements